

**IEEE JACK A. MORTON AWARD  
RECIPIENTS**

Beginning with the year 2000 presentation, the Jack A. Morton Award  
will be renamed the [IEEE Andrew S. Grove Award](#).

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|---|--|
| 1999 - CHARLES H. HENRY<br>Lucent Technologies, Bell Laboratories<br>Murray Hill, NJ  | "For fundamental contributions to the understanding of the optical properties of quantum wells and semiconductor lasers."                                  |
| 1998 - ISAMU AKASAKI<br>Meijo University<br>Nagoya, Japan<br>and SHUJI NAKAMURA<br>Nichia Chemical Industries, Ltd.<br>Tokushima, Japan   | "For contributions in the field of group-III nitride materials and devices."   |
| 1997 - CHENMING HU<br>University of California<br>Berkeley, CA  | "For outstanding contributions to the physics and modeling of MOS device reliability."   |
| 1996 - ROBERT W. DUTTON<br>Stanford University<br>Stanford, CA  | "For seminal contributions to semiconductor process and device modeling."  |
| 1995 - YOSHIO NISHI<br>Hewlett-Packard Company<br>Palo Alto, CA   | "For contributions to the basic understanding and innovative development of MOS device technology."  |
| 1994 - ROBERT E. KERWIN<br>AT&T<br>Warren, NJ<br>and DONALD L. KLEIN<br>IBM Corporation<br>Hopewell Junction, NY<br>and JOHN C. SARACE<br>Rockwell International<br>Anaheim, CA | "For pioneering work and the basic patent on the self-aligned silicon-gate process, a key element in fabrication of very large scale integrated circuits." |
| 1993 - TOSHIHISA TSUKADA<br>Hitachi, Ltd.<br>Tokyo, Japan   | "For contributions to the discovery and development of Buried Heterostructure (BH) semiconductor lasers."  |
| 1992 - TAKUO SUGANO<br>University of Tokyo<br>Tokyo, Japan  | "For contributions to Metal-Insulator-Semiconductor Devices and Technology."   |
| 1991 - TAK H. NING<br>HWA N. YU<br>IBM Corporation<br>Yorktown Height, NY   | "For contributions to the development of advanced bipolar and MOS devices."  |

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| 1990 - GREGORY E. STILLMAN<br>University of Illinois<br>Urbana, IL<br>and CHARLES M. WOLFE<br>Washington University<br>St. Louis, MO                    | "For the growth and characterization of ultra-high purity gallium arsenide and related compounds."  |
| 1989 - CHIH-TANG SAH<br>University of Illinois<br>Urbana, IL  | "For contributions to the understanding of semiconductor defects and the physics of MOS devices."   |
| 1988 - FRANK STERN<br>IBM Corp.<br>Yorktown Heights, NY   | "For contributions to the theory of injection lasers and two-dimensional electron gases."   |
| 1987 - DENNIS D. BUSS<br>and RICHARD A. CHAPMAN<br>and MICHAEL A. KINCH<br>Texas Instruments<br>Dallas, TX  | "For the demonstration and development of mercury cadmium telluride monolithically-integrated charge-coupled device focal plane arrays."                            |
| 1986 - HERBERT KROEMER<br>University of California<br>Santa Barbara, CA   | "For pioneering the theory and device applications of semiconductor heterostructures."  |
| 1985 - ROBERT D. BURNHAM<br>and WILLIAM STREIFER<br>Xerox Corp.<br>Palo Alto, CA<br>and DONALD R. SCIFRES<br>Spectra Diode Laboratories<br>San Jose, CA | "For contributions to electrically pumped distributed feedback lasers and high-power phased-locked laser arrays."   |
| 1984 - HANS S. RUPPRECHT<br>and JERRY M. WOODALL<br>IBM Corp.<br>Yorktown Heights, NY   | "For pioneering work in gallium aluminum arsenide heterojunctions and high efficiency light emitting diodes and injection lasers prepared by liquid phase epitaxy." |
| 1983 - JUN-ICHI NISHIZAWA<br>Tohoku University<br>Sendai, Japan   | "For invention and development of the class of static induction transistors (SIT) and for advances in optoelectronic devices."                                      |
| 1982 - DOV FROHMAN-BENTCHKOWSKY<br>INTEL Elec.<br>Jerusalem, Israel   | "For contributions to non-volatile semiconductor memories."   |
| 1981 - NICK HOLONYAK, JR.<br>University of Illinois<br>Urbana, IL   | "For pioneering work in quantum well lasers and contributions to visible semiconductor lasers and light-emitting diodes."   |

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| 1980 - JAMES F. GIBBONS<br>Stanford University<br>Stanford, CA    | "For pioneering contributions to the use of ion implantation in the fabrication of semiconductor devices."                     |
| 1979 - MARTIN P. LEPELTER<br>Bell Laboratories<br>Murray Hill, NJ | "For invention of the beam-lead structure and metallurgy used in silicon integrated circuits."                                 |
| 1978 - JURI MATISOO<br>IBM Corp.<br>Yorktown Heights, NY          | "For pioneering the Josephson computer technology."  |
| 1977 - MORGAN SPARKS<br>Sandia Corp.<br>Albuquerque, NM           | "For contributions to solid-state device technology and the management of research and development."                           |
| 1976 - ROBERT N. HALL<br>General Electric Co.<br>Schenectady, NY  | "For outstanding achievement in solid-state physics and chemistry and the invention and development of semiconductor devices." |